

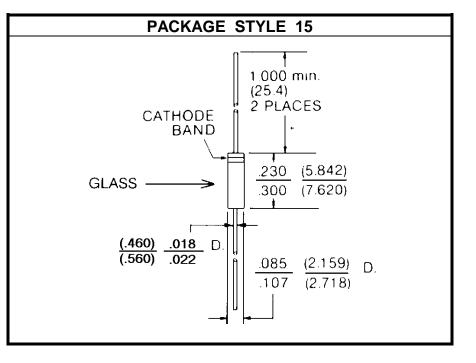
# SILICON ABRUPT JUNCTION TUNING VARACTOR

### **DESCRIPTION:**

The **AT6019M** is an Epitaxial Silicon Abrupt Junction Microwave Tuning Varactor. This Device is Passivated With Silicon Dioxide Which Results in Very Low Leakage Current. The Capacitance Voltage Relationship Closley Approximates Square Law (n = 0.5).

#### **MAXIMUM RATINGS**

| I <sub>c</sub>    | 100 mA                                    |  |  |  |  |
|-------------------|---|--|--|--|--|
| $V_{CE}$          | 70 V                                      |  |  |  |  |
| P <sub>DISS</sub> | 250 mW @ $T_c = 25 \ ^{\circ}C$           |  |  |  |  |
| TJ                | -65 <sup>o</sup> C to +150 <sup>o</sup> C |  |  |  |  |
| T <sub>STG</sub>  | -65 <sup>o</sup> C to +150 <sup>o</sup> C |  |  |  |  |



#### CHARACTERISTICS T<sub>c</sub> = 25 °C

| SYMBOL          | TEST CONDITIONS                                |             | MINIMUM | TYPICAL | MAXIMUM | UNITS               |
|-----------------|--|-------------|---------|---------|---------|---------------------|
| V <sub>B</sub>  | I <sub>R</sub> = 10 μA                         |             | 70      |         |         | V                   |
| CT              | V <sub>R</sub> = 4.0 V                         | f = 1.0 MHz | 31.35   | 33.0    | 34.65   | pF                  |
| ΔCT             | $C_{T} = 0 V / C_{T} = 60 V$                   | f = 1.0 MHz | 7.4     |         |         | RATIO               |
| ΔC <sub>T</sub> | $C_{T} = 8.0 \text{ V} / C_{T} = 60 \text{ V}$ | f = 1.0 MHz | 2.50    |         | 2.60    | RATIO               |
| Q               | V <sub>R</sub> = 4.0 V                         | f = 50 MHz  | 800     |         |         |                     |
| Tc              | V <sub>R</sub> = 4.0 V                         |             |         |         | 300     | Ppm/ <sup>o</sup> C |

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